

EPC2012 Information



For Reference Only

Part Number EPC2012 Manufacturer EPC

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description TRANS GAN 200V 3A BUMPED DIE

Package Die

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









EPC2012 Specifications

Manufacturer Part Number	EPC2012
Manufacturer	EPC
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	Die
Series	eGaN?
FET Type	N-Channel
Technology	GaNFET (Gallium Nitride)
Drain to Source Voltage (Vdss)	200V
Current - Continuous Drain (Id) @ 25°C	3A (Ta)
Drive Voltage (Max Rds On, Min Rds On)	5V
Vgs(th) (Max) @ Id	2.5V @ 1mA
Gate Charge (Qg) (Max) @ Vgs	1.8nC @ 5V
Input Capacitance (Ciss) (Max) @ Vds	145pF @ 100V
Vgs (Max)	+6V, -5V
FET Feature	-
Power Dissipation (Max)	-
Rds On (Max) @ Id, Vgs	100 mOhm @ 3A, 5V
Operating Temperature	-40°C ~ 125°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	Die
Package / Case	Die
	Report errors?

EPC2012 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

EPC2012 Payment Methods

































If you have any question about EPC2012, please do not hesitate to contact us!

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